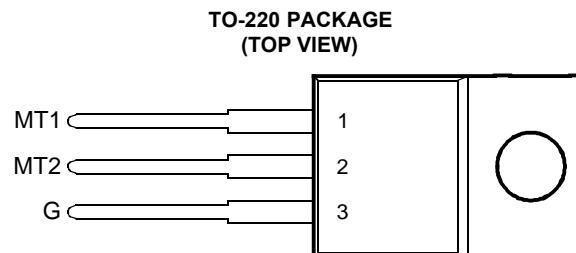


- 8 A RMS
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I_{GT} of 50 mA (Quadrants 1 - 3)



Pin 2 is in electrical contact with the mounting base.

MDC2ACA

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	TIC226D	400	V
	TIC226M	600	
	TIC226S	700	
	TIC226N	800	
Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2)	$I_{T(RMS)}$	8	A
Peak on-state surge current full-sine-wave at (or below) 25°C case temperature (see Note 3)	I_{TSM}	70	A
Peak gate current	I_{GM}	± 1	A
Peak gate power dissipation at (or below) 85°C case temperature (pulse width $\leq 200 \mu s$)	P_{GM}	2.2	W
Average gate power dissipation at (or below) 85°C case temperature (see Note 4)	$P_{G(AV)}$	0.9	W
Operating case temperature range	T_C	-40 to +110	°C
Storage temperature range	T_{stg}	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds	T_L	230	°C

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
 2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 320 mA/°C.
 3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
 4. This value applies for a maximum averaging time of 20 ms.

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DRM} Repetitive peak off-state current	V_D = rated V_{DRM}	$I_G = 0$	$T_C = 110^\circ C$			± 2	mA
I_{GT} Gate trigger current	$V_{supply} = +12 V \dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		6	50	mA
	$V_{supply} = +12 V \dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		-12	-50	
	$V_{supply} = -12 V \dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		-10	-50	
	$V_{supply} = -12 V \dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		25		
V_{GT} Gate trigger voltage	$V_{supply} = +12 V \dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		0.7	2	V
	$V_{supply} = +12 V \dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		-0.8	-2	
	$V_{supply} = -12 V \dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		-0.8	-2	
	$V_{supply} = -12 V \dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		0.9	2	
V_T On-state voltage	$I_T = \pm 12 A$	$I_G = 50 mA$	(see Note 5)		± 1.5	± 2.1	V
I_H Holding current	$V_{supply} = +12 V \dagger$	$I_G = 0$	$Init' I_{TM} = 100 mA$		10	30	mA
	$V_{supply} = -12 V \dagger$	$I_G = 0$	$Init' I_{TM} = -100 mA$		-6	-30	

† All voltages are with respect to Main Terminal 1.

PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.

TIC226 SERIES SILICON TRIACS

APRIL 1971 - REVISED DECEMBER 2000

electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_L	Latching current	$V_{\text{supply}} = +12 \text{ V} \dagger$ $V_{\text{supply}} = -12 \text{ V} \dagger$ (see Note 6)			50 -50	mA
dv/dt	Critical rate of rise of off-state voltage	$V_{\text{DRM}} = \text{Rated } V_{\text{DRM}}$ $I_G = 0$ $T_C = 110^\circ\text{C}$		± 100		V/μs
$dv/dt_{(c)}$	Critical rise of commutation voltage	$V_{\text{DRM}} = \text{Rated } V_{\text{DRM}}$ $I_{\text{TRM}} = \pm 12 \text{ A}$ $T_C = 85^\circ\text{C}$ (see figure 7)	± 5			V/μs

† All voltages are with respect to Main Terminal 1.

NOTES: 5. This parameter must be measured using pulse techniques, $t_p = \leq 1 \text{ ms}$, duty cycle $\leq 2 \%$. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

6. The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G = 100 \Omega$, $t_{p(g)} = 20 \mu\text{s}$, $t_r = \leq 15 \text{ ns}$, $f = 1 \text{ kHz}$.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta\text{JC}}$	Junction to case thermal resistance			1.8	°C/W
$R_{\theta\text{JA}}$	Junction to free air thermal resistance			62.5	°C/W

TYPICAL CHARACTERISTICS

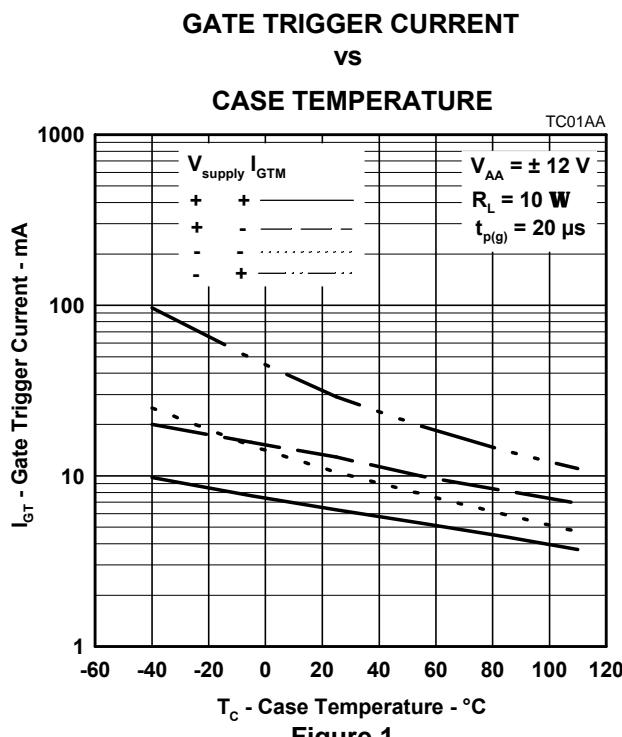


Figure 1.

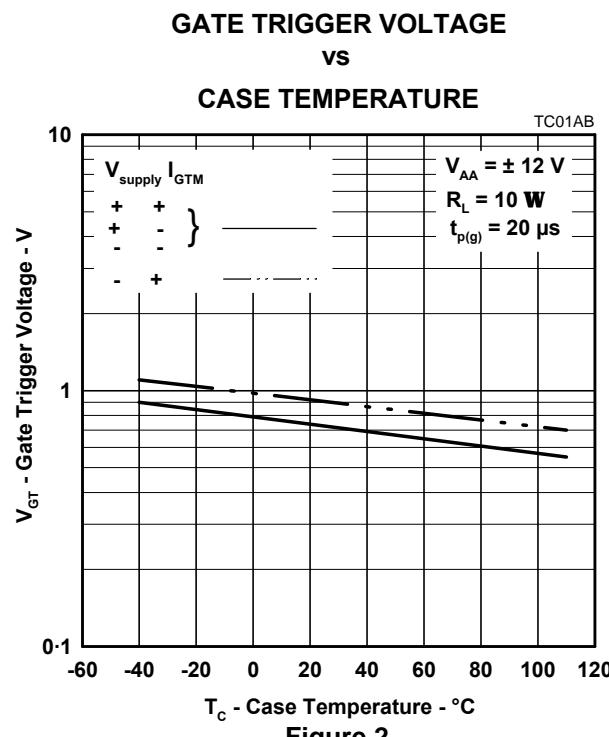


Figure 2.

PRODUCT INFORMATION

TYPICAL CHARACTERISTICS

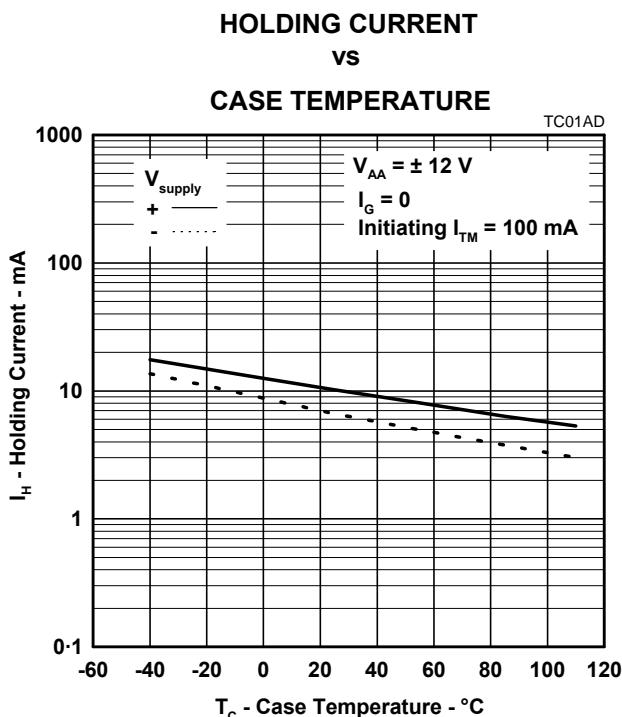


Figure 3.

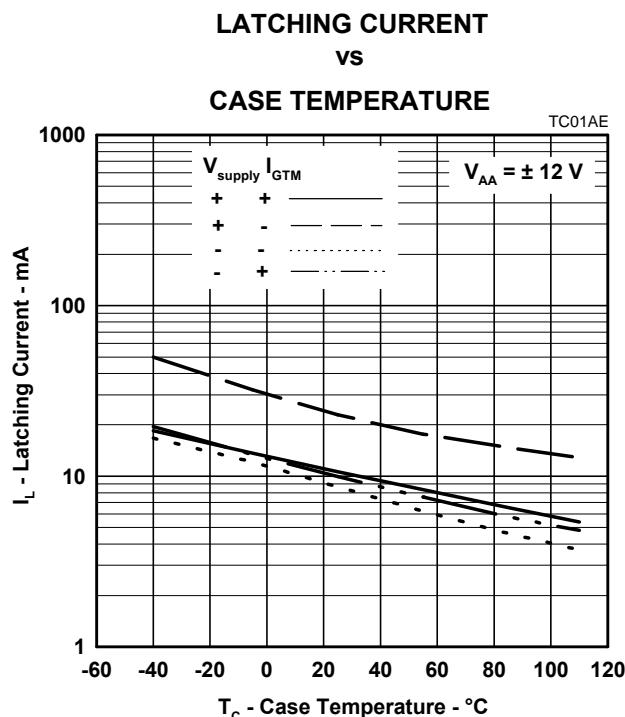


Figure 4.

THERMAL INFORMATION

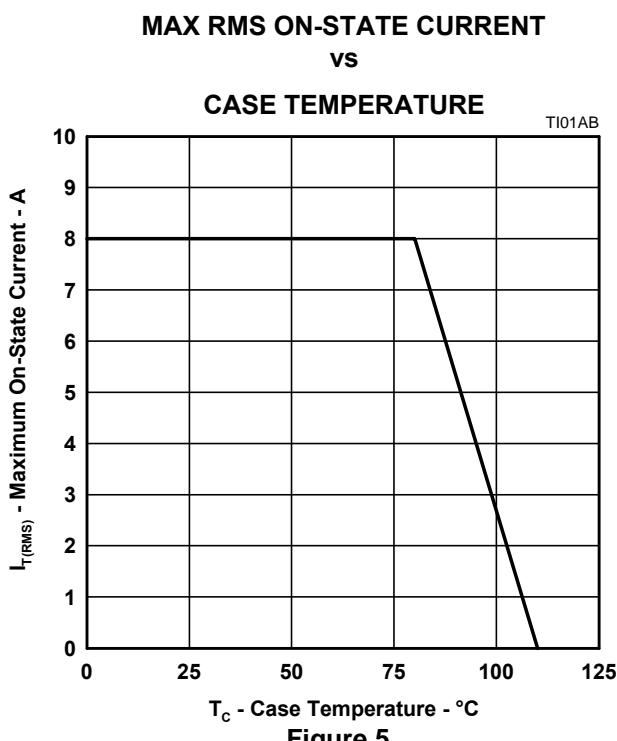


Figure 5.

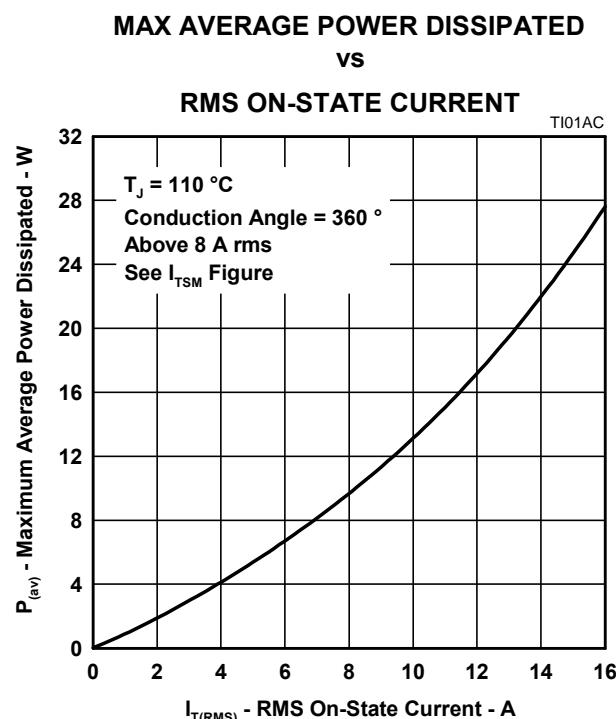
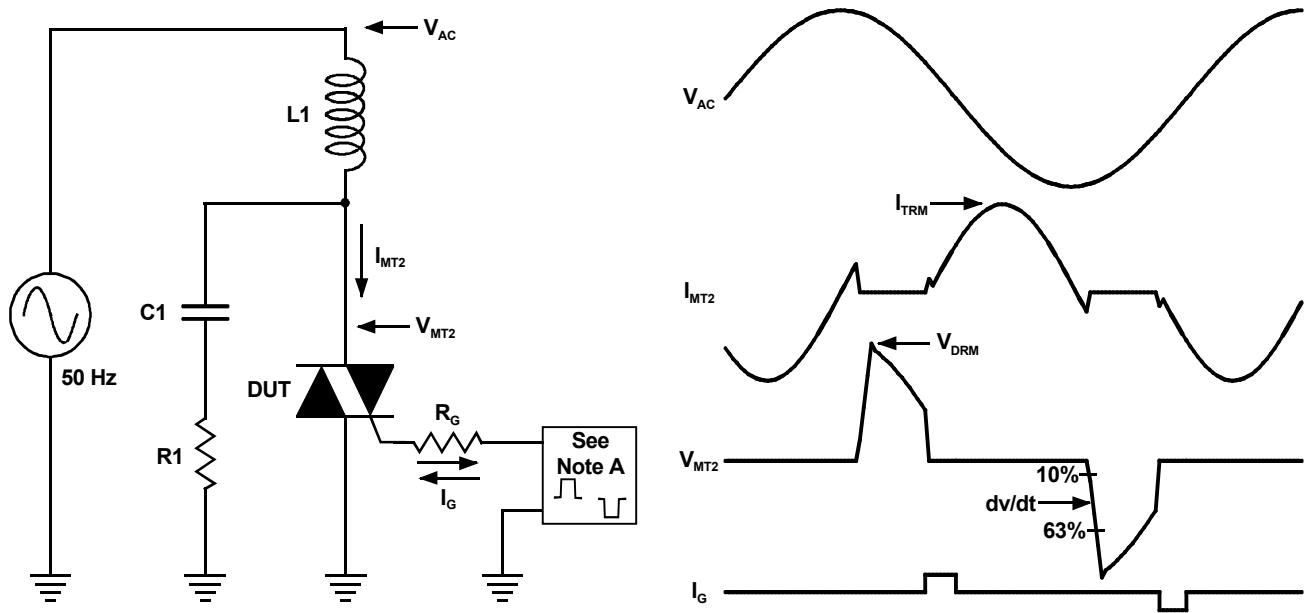


Figure 6.

TIC226 SERIES SILICON TRIACS

APRIL 1971 - REVISED DECEMBER 2000

PARAMETER MEASUREMENT INFORMATION



NOTE A: The gate-current pulse is furnished by a trigger circuit which presents essentially an open circuit between pulses. The pulse is timed so that the off-state-voltage duration is approximately 800 μ s.

PMC2AA

Figure 7.

PRODUCT INFORMATION

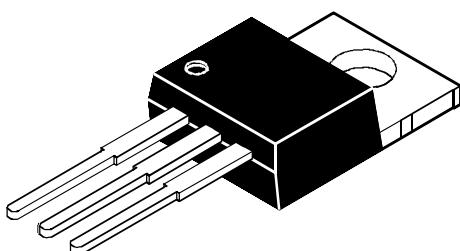
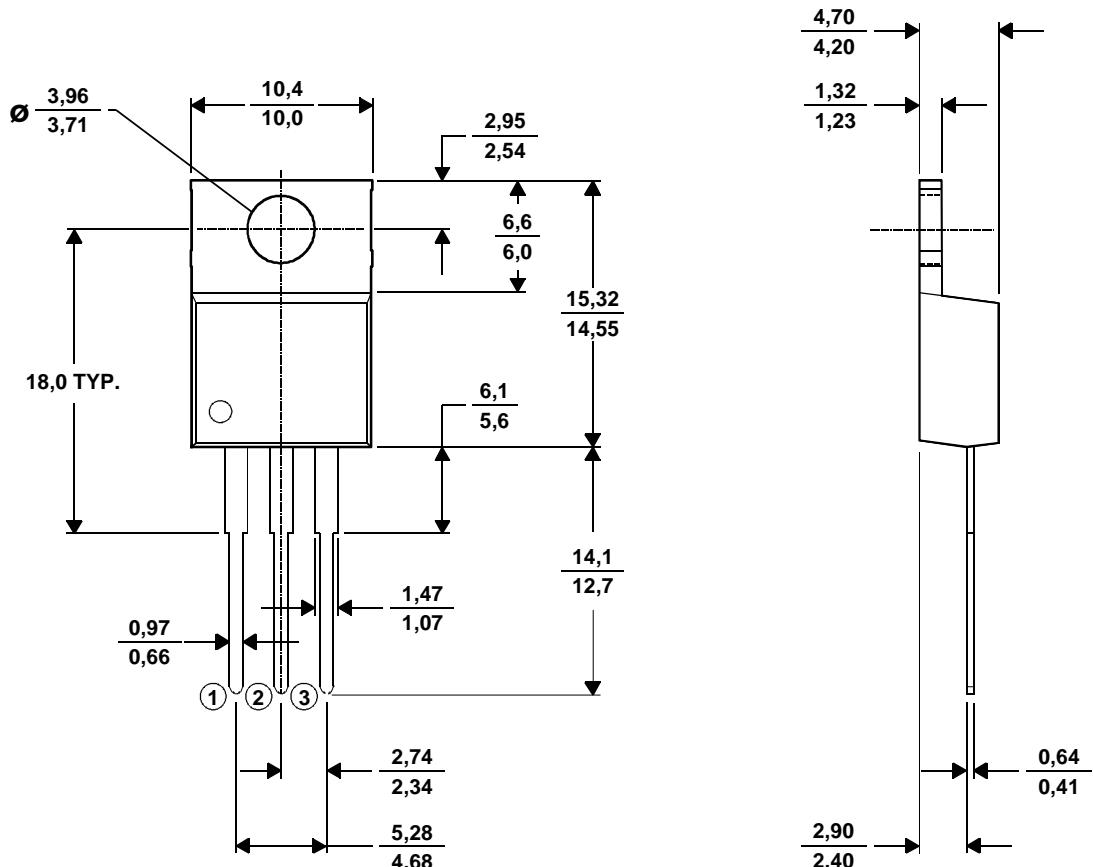
MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.

TO-220



ALL LINEAR DIMENSIONS IN MILLIMETERS

NOTE A: The centre pin is in electrical contact with the mounting tab.

TIC226 SERIES SILICON TRIACS

APRIL 1971 - REVISED DECEMBER 2000

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